



ON Semiconductor®

# FQT3P20

## P-Channel QFET® MOSFET

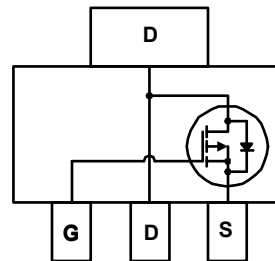
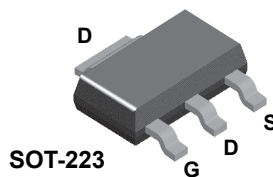
-200 V, -0.67 A, 2.7 Ω

### Features

- -0.67 A, -200 V,  $R_{DS(on)} = 2.7 \Omega$  (Max.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 0.335 \text{ A}$
- Low Gate Charge (Typ. 6.0 nC)
- Low Crss (Typ. 7.5 pF)

### Description

This P-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FQT3P20TF	Unit
$V_{DSS}$	Drain-Source Voltage	-200	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 70^\circ\text{C}$ )	-0.67	A
		-0.53	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	-2.7	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	150	mJ
$I_{AR}$	Avalanche Current (Note 1)	-0.67	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	0.25	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-5.5	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	2.5	W
		0.02	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FQT3P20TF	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	$^\circ\text{C}/\text{W}$

FQT3P20 — P-Channel QFET® MOSFET

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQT3P20	FQT3P20TF	SOT-223	13"	12 mm	2500 units

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-200	--	--	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.18	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{DS} = -160\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-3.0	--	-5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -0.335\text{ A}$	--	2.06	2.7	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -0.335\text{ A}$	--	0.7	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	190	250	pF
$C_{oss}$	Output Capacitance		--	45	60	pF
$C_{riss}$	Reverse Transfer Capacitance		--	7.5	10	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -100\text{ V}, I_D = -2.8\text{ A},$ $R_G = 25\ \Omega$	--	8.5	25	ns
$t_r$	Turn-On Rise Time		--	35	80	ns
$t_{d(off)}$	Turn-Off Delay Time		--	12	35	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	25	60
$Q_g$	Total Gate Charge	$V_{DS} = -160\text{ V}, I_D = -2.8\text{ A},$ $V_{GS} = -10\text{ V}$	--	6.0	8.0	nC
$Q_{gs}$	Gate-Source Charge		--	1.7	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	2.9	--

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	-0.67	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-2.7	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.67\text{ A}$	--	--	-5.0	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -2.8\text{ A},$	--	100	--	ns
$Q_{rr}$	Reverse Recovery Charge	$dI_F / dt = 100\text{ A}/\mu\text{s}$	--	0.34	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 500\text{mH}, I_{AS} = -0.67\text{ A}, V_{DD} = -50\text{ V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -2.8\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

## Typical Characteristics

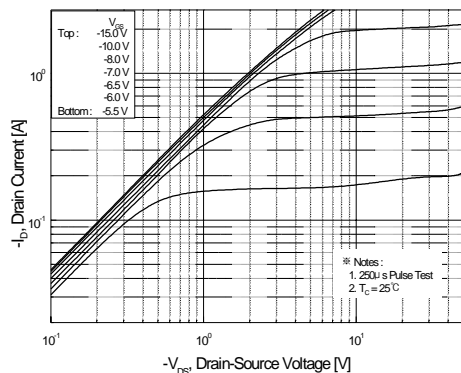


Figure 1. On-Region Characteristics

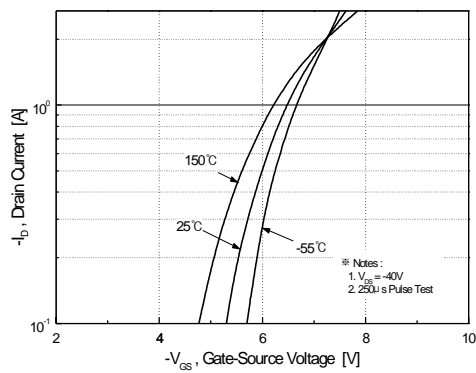


Figure 2. Transfer Characteristics

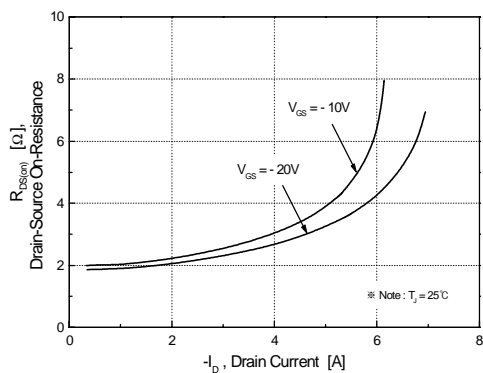


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

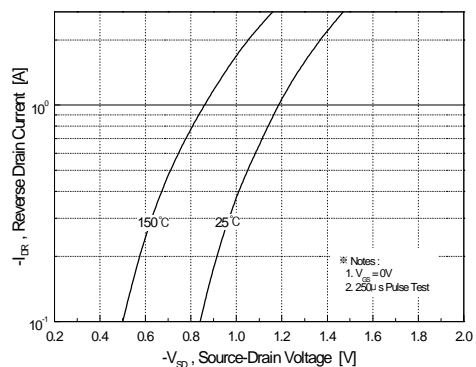


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

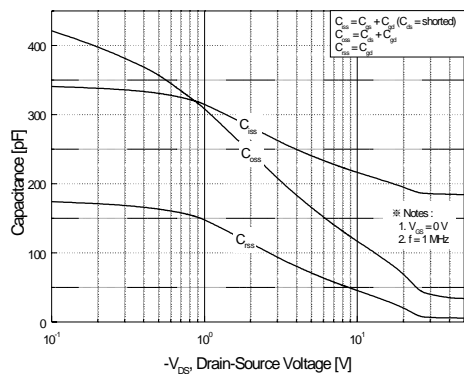


Figure 5. Capacitance Characteristics

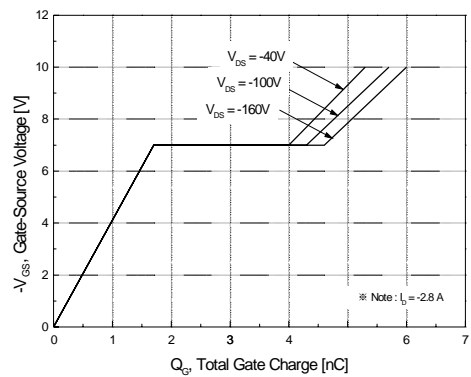


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

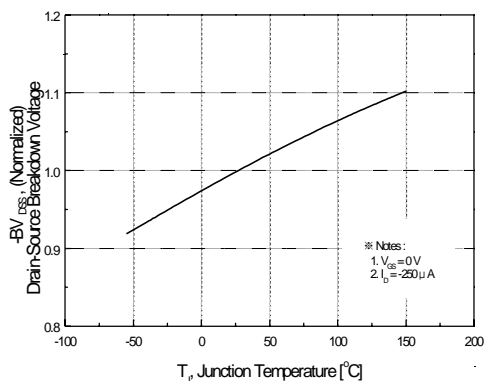


Figure 7. Breakdown Voltage Variation vs. Temperature

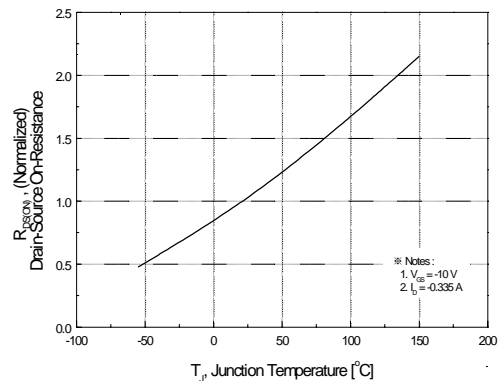


Figure 8. On-Resistance Variation vs. Temperature

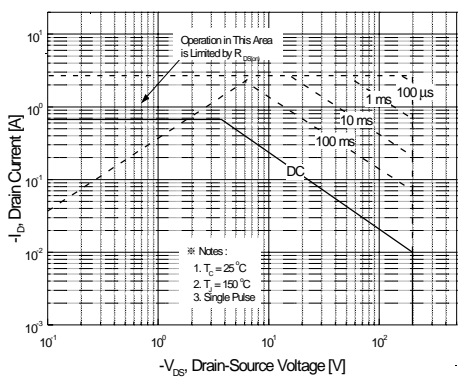


Figure 9. Maximum Safe Operating Area

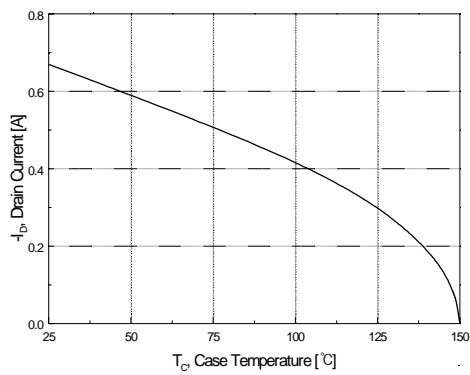


Figure 10. Maximum Drain Current vs. Case Temperature

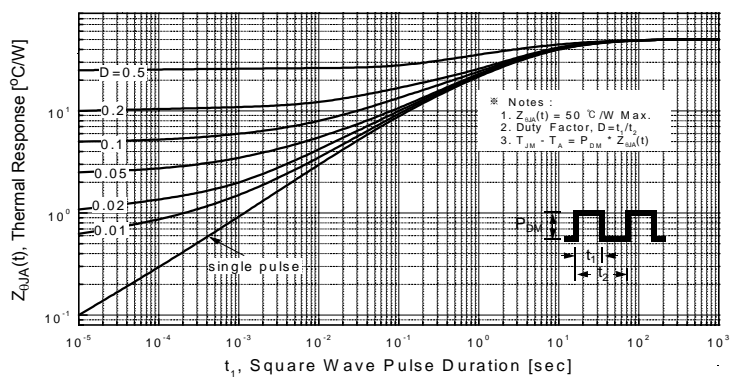
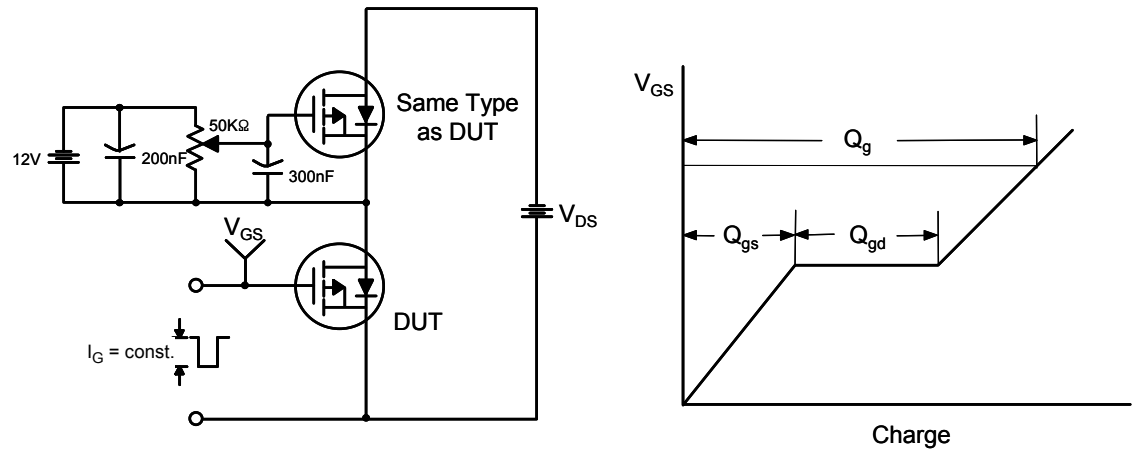
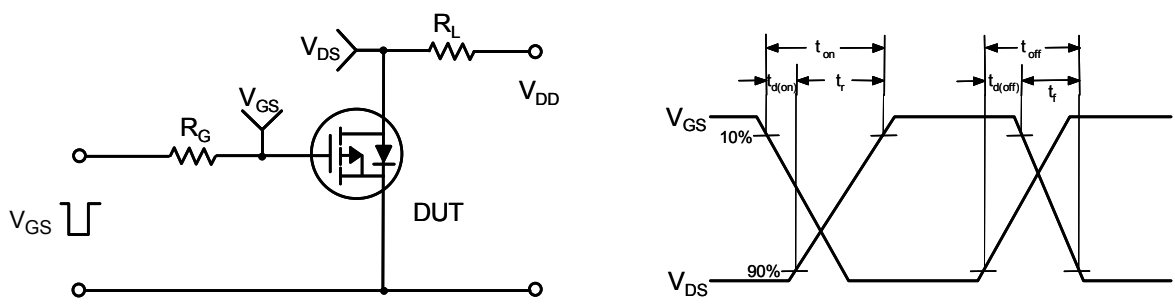


Figure 11. Transient Thermal Response Curve

**Figure 12. Gate Charge Test Circuit & Waveform**



**Figure 13. Resistive Switching Test Circuit & Waveforms**



**Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms**

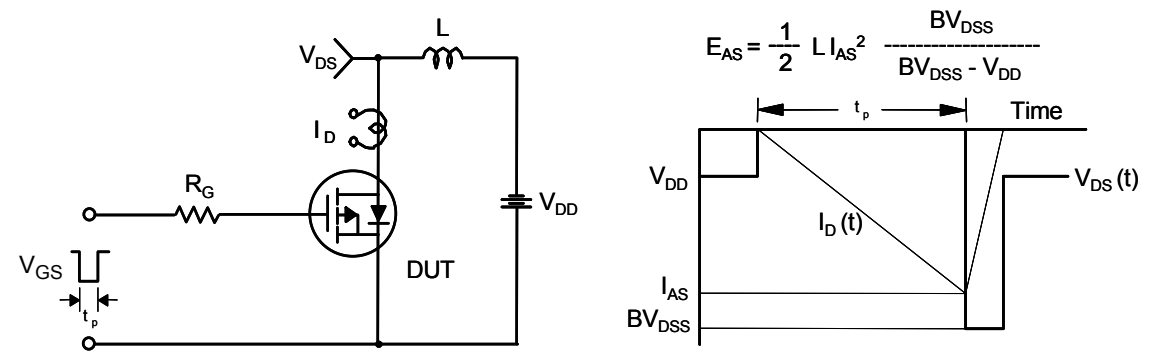
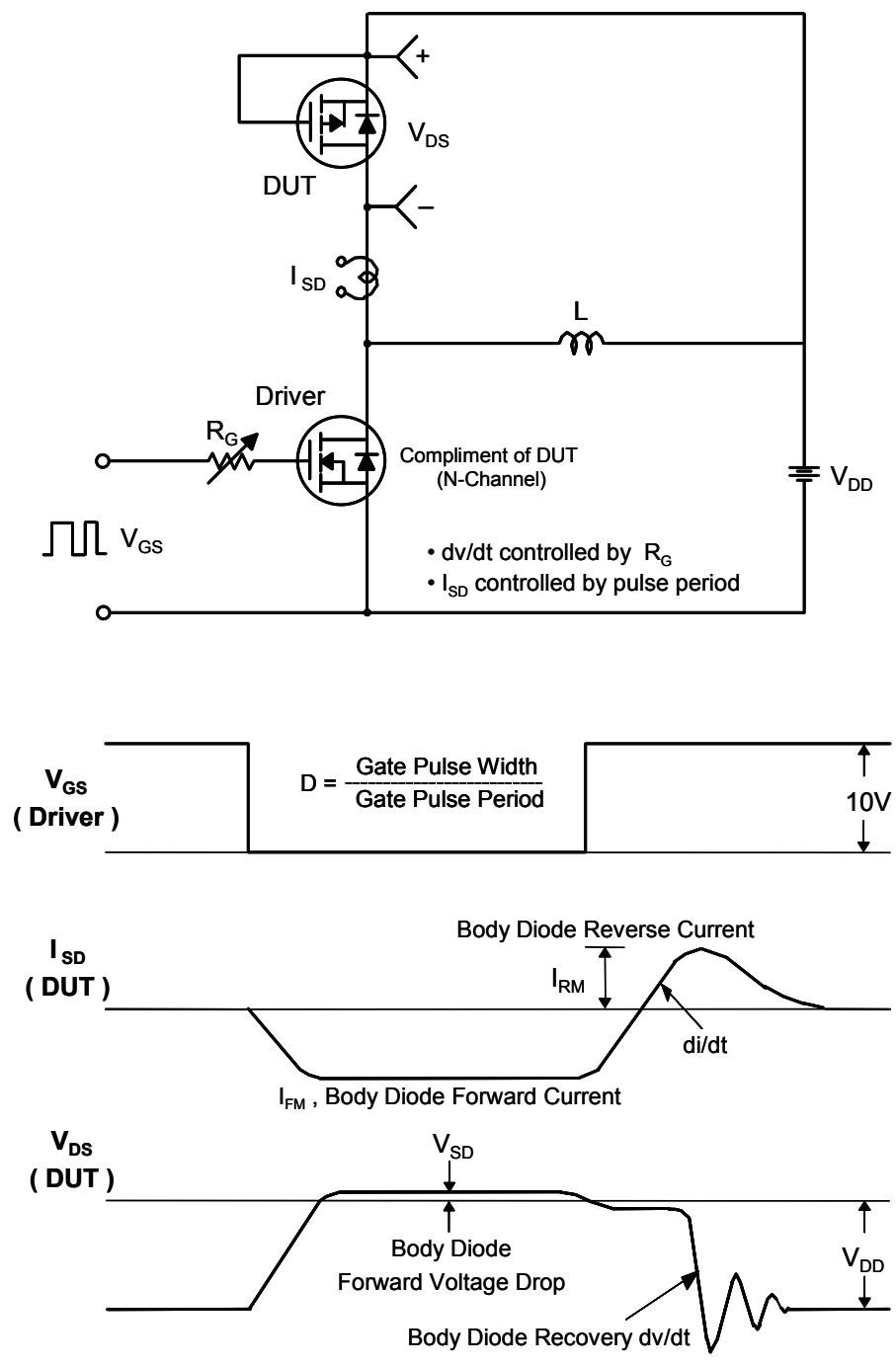
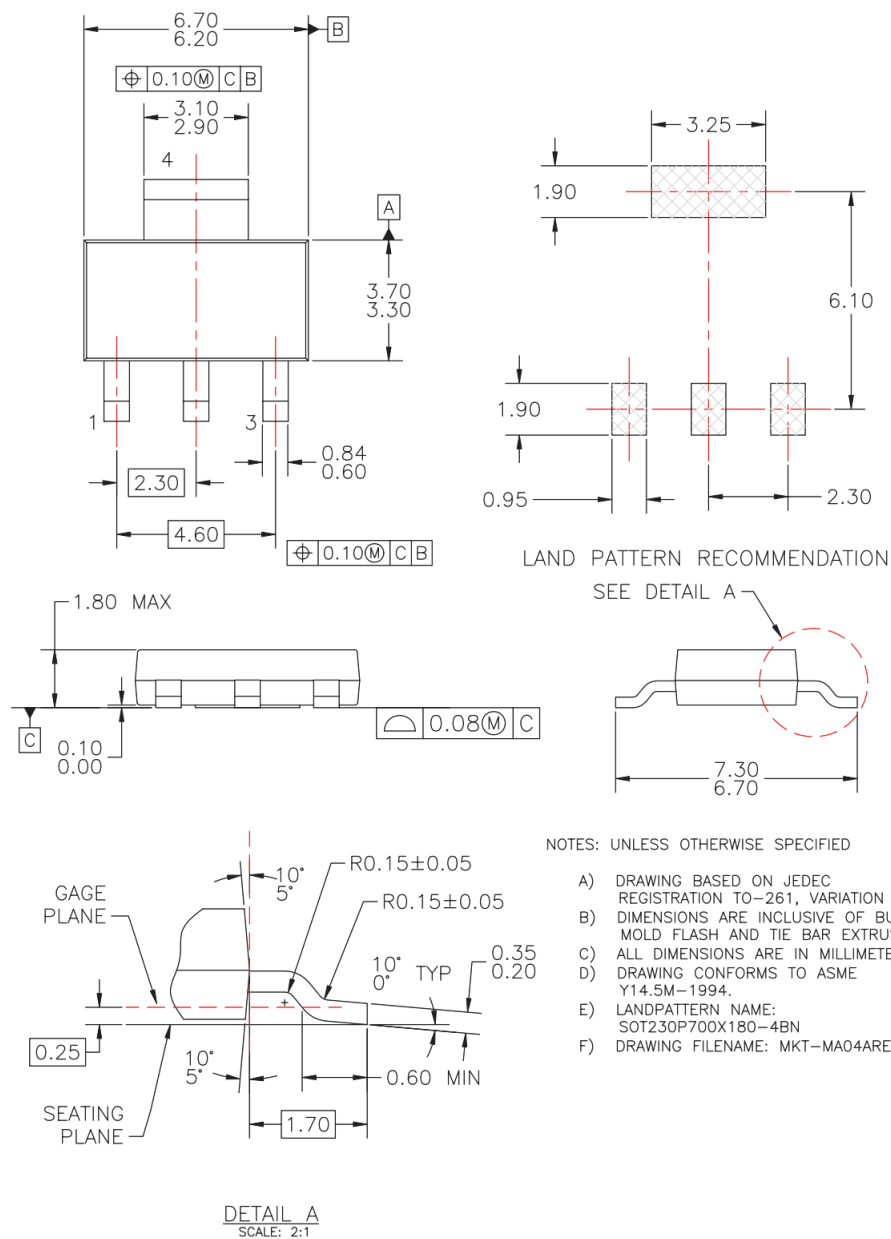


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



## Mechanical Dimensions

### SOT-223 4L



**Figure 16. Molded Package, SOT-223, 4 Lead**

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Dimension in Millimeters

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